

CD4076BMS

CMOS 4 -Bit D-Type Registers

FN3325 Rev 0.00 December 1992

Features

- · High Voltage Type (20V Rating)
- Three State Outputs
- Input Disabled Without Gating the Clock
- Gated Output Control Lines for Enabling or Disabling the Outputs
- Standardized Symmetrical Output Characteristics
- 100% Tested for Quiescent Current at 20V
- Maximum Input Current of 1μA at 18V Over Full Package Temperature Range; 100nA at 18V and +25°C
- Noise Margin (Over Full Package/Temperature Range)
 - 1V at VDD = 5V
 - 2V at VDD = 10V
 - 2.5V at VDD = 15V
- · 5V, 10V and 15V Parametric Ratings
- Meets All Requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"

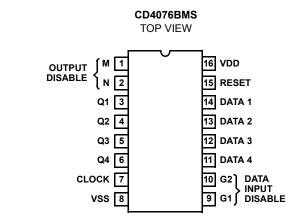
Description

CD4076BMS types are four-bit registers consisting of D-type flip-flops that feature three-state outputs. Data Disable inputs are provided to control the entry of data into the flip-flops. When both Data Disable inputs are low, data at the D inputs are loaded into their respective flip-flops on the next positive transition of the clock input. Output Disable inputs are also provided. When the Output Disable inputs are both low, the normal logic states of the four outputs are available to the load. The outputs are disabled independently of the clock by a high logic level at either Output Disable input, and present a high impedance.

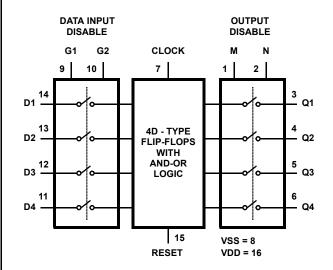
The CD4076BMS is supplied in these 16 lead outline packages:

Braze Seal DIP H4T
Frit Seal DIP H1E
Ceramic Flatpack H6W

Pinout



Functional Diagram



Absolute Maximum Ratings

Reliability Information

| Thermal Resistance | θ_{ia} | $\theta_{\sf ic}$ |
|--|---------------|-------------------|
| Ceramic DIP and FRIT Package | 80°C/W | 20°C/W |
| Flatpack Package | 70°C/W | 20°C/W |
| Maximum Package Power Dissipation (PD |) at +125°C |) |
| For TA = -55°C to +100°C (Package Typ | oe D, F, K). | 500mW |
| For TA = +100°C to +125°C (Package T | ype D, F, K |) Derate |
| Lineari | ty at 12mW | /OC to 200mW |
| Device Dissipation per Output Transistor . | | 100mW |
| For TA = Full Package Temperature Rar | nge (All Pac | kage Types) |
| Junction Temperature | | +175°C |

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS

| | | | | GROUP A | | LIN | IITS | |
|--------------------------------|--------|---------------------------------------|---------------|----------------|--------------------------|-------|-------|----------------|
| PARAMETER | SYMBOL | CONDITIONS (N | NOTE 1) | SUB- GROUPS | TEMPERATURE | MIN | MAX | UNIT S |
| Supply Current | IDD | VDD = 20V, VIN = VD | D or GND | 1 | +25°C | - | 10 | μА |
| | | | | 2 | +125°C | - | 1000 | μА |
| | | VDD = 18V, VIN = VD | D or GND | 3 | -55°C | - | 10 | μА |
| Input Leakage Current | IIL | VIN = VDD or GND | VDD = 20 | 1 | +25°C | -100 | - | nA |
| | | | | 2 | +125°C | -1000 | - | nA |
| | | | | 3 | -55°C | -100 | - | nA |
| Input Leakage Current | IIH | VIN = VDD or GND | VDD = 20 | 1 | +25°C | - | 100 | nA |
| | | | | 2 | +125°C | - | 1000 | nA |
| | | | VDD = 18V | 3 | -55°C | - | 100 | nA |
| Output Voltage | VOL15 | VDD = 15V, No Load | | 1, 2, 3 | +25°C, +125°C, - 55°C | - | 50 | mV |
| Output Voltage | VOH15 | VDD = 15V, No Load | , | 1, 2, 3 | +25°C, +125°C, - 55°C | 14.95 | - | V |
| Output Current (Sink) | IOL5 | VDD = 5V, VOUT = 0. | 4V | 1 | +25°C | 0.53 | - | mA |
| Output Current (Sink) | IOL10 | VDD = 10V, VOUT = 0 | 0.5V | 1 | +25°C | 1.4 | - | mΑ |
| Output Current (Sink) | IOL15 | VDD = 15V, VOUT = 1.5V | | 1 | +25°C | 3.5 | - | mA |
| Output Current (Source) | IOH5A | VDD = 5V, VOUT = 4.6V | | 1 | +25°C | - | -0.53 | mA |
| Output Current (Source) | IOH5B | VDD = 5V, VOUT = 2.5V | | 1 | +25°C | - | -1.8 | mA |
| Output Current (Source) | IOH10 | VDD = 10V, VOUT = 9.5V | | 1 | +25°C | - | -1.4 | mA |
| Output Current (Source) | IOH15 | VDD = 15V, VOUT = 1 | 13.5V | 1 | +25°C | - | -3.5 | mA |
| N Threshold Voltage | VNTH | VDD = 10V, ISS = -10 | μΑ | 1 | +25°C | -2.8 | -0.7 | V |
| P Threshold Voltage | VPTH | VSS = 0V, IDD = 10μ/ | 4 | 1 | +25°C | 0.7 | 2.8 | V |
| Functional | F | VDD = 2.8V, VIN = V | DD or GND | 7 | +25°C | VOH> | VOL < | V |
| | | VDD = 20V, VIN = VD | D or GND | 7 | +25°C | VDD/2 | VDD/2 | |
| | | VDD = 18V, VIN = VD | D or GND | 8A | +125°C | | | |
| | | VDD = 3V, VIN = VDD | or GND | 8B | -55°C | | | |
| Input Voltage Low (Note 2) | VIL | VDD = 5V, VOH > 4.5 | V, VOL < 0.5V | 1, 2, 3 | +25°C, +125°C, - 55°C | - | 1.5 | V |
| Input Voltage High (Note 2) | VIH | VDD = 5V, VOH > 4.5 | V, VOL < 0.5V | 1, 2, 3 | +25°C, +125°C, - 55°C | 3.5 | - | V |
| Input Voltage Low (Note 2) | VIL | VDD = 15V, VOH > 13.5V, VOL < 1.5V | | 1, 2, 3 | +25°C, +125°C, - 55°C | - | 4 | V |
| Input Voltage High (Note 2) | VIH | VDD = 15V, VOH > 13 VOL < 1.5V | 3.5V, | 1, 2, 3 | +25°C, +125°C, - 55°C | 11 | - | V |
| Tri-State Output | IOZL | VIN = VDD or GND | VDD = 20V | 1 | +25°C | -0.4 | - | μΑ |
| Leakage | | VOUT = 0V | | 2 | +125°C | -12 | - | <u>.</u> μΑ |
| | | | VDD = 18V | 3 | -55°C | -0.4 | - | μ A |



TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS

| | | | | GROUP A | | | LIMITS | |
|------------------|--------|------------------|-----------|----------------|-------------|-----|--------|-----------|
| PARAMETER | SYMBOL | | | SUB- GROUPS | TEMPERATURE | MIN | MAX | UNIT S |
| Tri-State Output | IOZH | VIN = VDD or GND | VDD = 20V | 1 | +25°C | - | 0.4 | μА |
| Leakage | | VOUT = VDD | | 2 | +125°C | - | 12 | μА |
| | | | VDD = 18V | 3 | -55°C | - | 0.4 | μА |

NOTES: 1. All voltages referenced to device GND, 100% testing being implemented.

 For accuracy, voltage is measured differentially to VDD. Limit is 0.050V max.

2. Go/No Go test with limits applied to inputs.

TABLE 2. AC ELECTRICAL PERFORMANCE CHARACTERISTICS

| | | | GROUP A | | LIMITS | | |
|-------------------|--------|----------------------------|---------------|---------------|--------|-----|-------|
| PARAMETER | SYMBOL | CONDITIONS (Notes 1, 2) | SUBGROUPS | TEMPERATURE | MIN | MAX | UNITS |
| Propagation Delay | TPHL | VDD = 5V, VIN = VDD or GND | 9 | +25°C | - | 600 | ns |
| Clock to Q Output | TPLH | | 10, 11 | +125°C, -55°C | - | 810 | ns |
| Transition Time | TTHL | VDD = 5V, VIN = VDD or GND | 9 | +25°C | - | 200 | ns |
| TTLH | l | 10, 11 | +125°C, -55°C | - | 270 | ns | |

NOTES:

- 1. CL = 50pF, RL = 200K, Input TR, TF < 20ns.
- 2. -55°C and +125°C limits guaranteed, 100% testing being implemented.

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

| | | | | | LIN | MITS | |
|-------------------------|--------|-----------------------------|-------|-------------------------|------|-------|-------|
| PARAMETER | SYMBOL | CONDITIONS | NOTES | TEMPERATURE | MIN | MAX | UNITS |
| Supply Current | IDD | VDD = 5V, VIN = VDD or GND | 1, 2 | -55°C, +25°C | - | 5 | μΑ |
| | | | | +125°C | - | 150 | μА |
| | | VDD = 10V, VIN = VDD or GND | 1, 2 | -55°C, +25°C | - | 10 | μА |
| | | | | +125°C | - | 300 | μΑ |
| | | VDD = 15V, VIN = VDD or GND | 1, 2 | -55°C, +25°C | - | 10 | μΑ |
| | | | | +125°C | - | 600 | μА |
| Output Voltage | VOL | VDD = 5V, No Load | 1, 2 | +25°C, +125°C, -55°C | - | 50 | mV |
| Output Voltage | VOL | VDD = 10V, No Load | 1, 2 | +25°C, +125°C, -55°C | - | 50 | mV |
| Output Voltage | VOH | VDD = 5V, No Load | 1, 2 | +25°C, +125°C, -55°C | 4.95 | - | V |
| Output Voltage | VOH | VDD = 10V, No Load | 1, 2 | +25°C, +125°C, -55°C | 9.95 | - | V |
| Output Current (Sink) | IOL5 | VDD = 5V, VOUT = 0.4V | 1, 2 | +125°C | 0.36 | - | mA |
| | | | | -55°C | 0.64 | - | mA |
| Output Current (Sink) | IOL10 | VDD = 10V, VOUT = 0.5V | 1, 2 | +125°C | 0.9 | - | mA |
| | | | | -55°C | 1.6 | - | mA |
| Output Current (Sink) | IOL15 | VDD = 15V, VOUT = 1.5V | 1, 2 | +125°C | 2.4 | - | mA |
| | | | | -55°C | 4.2 | - | mA |
| Output Current (Source) | IOH5A | VDD = 5V, VOUT = 4.6V | 1, 2 | +125°C | - | -0.36 | mA |
| | | | | -55°C | - | -0.64 | mA |
| Output Current (Source) | IOH5B | VDD = 5V, VOUT = 2.5V | 1, 2 | +125°C | - | -1.15 | mA |
| | | | | -55°C | - | -2.0 | mA |
| Output Current (Source) | IOH10 | VDD = 10V, VOUT = 9.5V | 1, 2 | +125°C | - | -0.9 | mA |
| | | | | -55°C | - | -2.6 | mA |
| Output Current (Source) | IOH15 | VDD =15V, VOUT = 13.5V | 1, 2 | +125°C | - | -2.4 | mA |
| | | | | -55°C | - | -4.2 | mA |

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

| | | | | | LIN | IITS | |
|------------------------------|--------|-------------------------------|------------|-------------------------|-----|------|-------|
| PARAMETER | SYMBOL | CONDITIONS | NOTES | TEMPERATURE | MIN | MAX | UNITS |
| Input Voltage Low | VIL | VDD = 10V, VOH > 9V, VOL < 1V | 1, 2 | +25°C, +125°C, -55°C | - | 3 | V |
| Input Voltage High | VIH | VDD = 10V, VOH > 9V, VOL < 1V | 1, 2 | +25°C, +125°C, -55°C | 7 | - | V |
| Propagation Delay | TPHL1 | VDD = 10V | 1, 2, 3 | +25°C | - | 250 | ns |
| Clock to Q Output | TPLH1 | VDD = 15V | 1, 2, 3 | +25°C | - | 180 | ns |
| Propagation Delay | TPHL2 | VDD = 5V | 1, 2, 3 | +25°C | - | 460 | ns |
| Reset | | VDD = 10V | 1, 2, 3 | +25°C | - | 200 | ns |
| 1 | | VDD = 15V | 1, 2, 3 | +25°C | - | 150 | ns |
| Propagation Delay | TPHZ | VDD = 5V | 1, 2, 4 | +25°C | - | 300 | ns |
| 3 - State | TPLZ | VDD = 10V | 1, 2, 4 | +25°C | - | 150 | ns |
| l | | VDD = 15V | 1, 2, 4 | +25°C | - | 120 | ns |
| Propagation Delay | TPZH | VDD = 5V | 1, 2, 4 | +25°C | - | 300 | ns |
| 3 - State | TPZL | VDD = 10V | 1, 2, 4 | +25°C | - | 150 | ns |
| | | VDD = 15V | 1, 2, 4 | +25°C | - | 120 | ns |
| Transition Time | TTHL | VDD = 10V | 1, 2, 3 | +25°C | - | 100 | ns |
| l | TTLH | VDD = 15V | 1, 2, 3 | +25°C | - | 80 | ns |
| Transition Time | TTLH | VDD = 10V | 1, 2, 3 | +25°C | - | - | ns |
| | | VDD = 15V | 1, 2, 3 | +25°C | - | - | ns |
| Maximum Clock Input | FCL | VDD = 5V | 1, 2, 3 | +25°C | 3 | - | MHz |
| Maximum Clock Input requency | | VDD = 10V | 1, 2, 3 | +25°C | 6 | - | MHz |
| l | | VDD = 15V | 1, 2, 3 | +25°C | 8 | - | MHz |
| Minimum Data Setup | TS | VDD = 5V | 1, 2, 3 | +25°C | - | 200 | ns |
| Time | | VDD = 10V | 1, 2, 3 | +25°C | - | 80 | ns |
| l | | VDD = 15V | 1, 2, 3 | +25°C | - | 60 | ns |
| Minimum Data Hold Time | TW | VDD = 5V | 1, 2, 3 | +25°C | - | 120 | ns |
| Reset Pulse Width | | VDD = 10V | 1, 2, 3 | +25°C | - | 50 | ns |
| l | | VDD = 15V | 1, 2, 3 | +25°C | - | 40 | ns |
| Minimum Clock Pulse | TW | VDD = 5V | 1, 2, 3 | +25°C | - | 200 | ns |
| Width | | VDD = 10V | 1, 2, 3 | +25°C | - | 100 | ns |
| l | | VDD = 15V | 1, 2, 3 | +25°C | - | 80 | ns |
| Minimum Data Input Set- | TS | VDD = 5V | 1, 2, 3 | +25°C | - | 180 | ns |
| Up Time | | VDD = 10V | 1, 2, 3 | +25°C | - | 100 | ns |
| 1 | | VDD = 15V | 1, 2, 3 | +25°C | - | 70 | ns |
| Maximum Clock Input | TRCL | VDD = 5V | 1, 2, 3, 5 | +25°C | - | 15 | μS |
| Rise and Fall Time | TFCL | VDD = 10V | 1, 2, 3, 5 | +25°C | - | 5 | μS |
| 1 | | VDD = 15V | 1, 2, 3, 5 | +25°C | - | 5 | μS |
| Input Capacitance | CIN | Any Input | 1, 2 | +25°C | - | 7.5 | pF |

NOTES:

- 1. All voltages referenced to device GND.
- 2. The parameters listed on Table 3 are controlled via design or process and are not directly tested. These parameters are characterized on initial design release and upon design changes which would affect these characteristics.
- 3. CL = 50pF, RL = 200K, Input TR, TF < 20ns.
- 4. CL = 50pF, RL = 1K, Input TR, TF < 20ns.
- 5. If more than one unit is cascaded, TRCL should be made less than or equal to the sum of the transition time and the fixed propagation delay of the output of the driving stage for the estimated capacitive load.



TABLE 4. POST IRRADIATION ELECTRICAL PERFORMANCE CHARACTERISTICS

| | | | | | LIM | ITS | |
|------------------------------|--------------|-----------------------------|------------|-------------|-------|--------------------------|-------|
| PARAMETER | SYMBOL | CONDITIONS | NOTES | TEMPERATURE | MIN | MAX | UNITS |
| Supply Current | IDD | VDD = 20V, VIN = VDD or GND | 1, 4 | +25°C | - | 25 | μΑ |
| N Threshold Voltage | VNTH | VDD = 10V, ISS = -10μA | 1, 4 | +25°C | -2.8 | -0.2 | V |
| N Threshold Voltage Delta | ΔVTN | VDD = 10V, ISS = -10μA | 1, 4 | +25°C | - | ±1 | V |
| P Threshold Voltage | VTP | VSS = 0V, IDD = 10μA | 1, 4 | +25°C | 0.2 | 2.8 | V |
| P Threshold Voltage Delta | ΔVΤΡ | VSS = 0V, IDD = 10μA | 1, 4 | +25°C | - | ±1 | V |
| Functional | F | VDD = 18V, VIN = VDD or GND | 1 | +25°C | VOH > | VOL < | V |
| | | VDD = 3V, VIN = VDD or GND | | | VDD/2 | VDD/2 | |
| Propagation Delay Time | TPHL TPLH | VDD = 5V | 1, 2, 3, 4 | +25°C | - | 1.35 x +25°C Limit | ns |

NOTES: 1. All voltages referenced to device GND.

3. See Table 2 for +25°C limit.

2. CL = 50pF, RL = 200K, Input TR, TF < 20ns.

4. Read and Record

TABLE 5. BURN-IN AND LIFE TEST DELTA PARAMETERS +25°C

| PARAMETER | SYMBOL | DELTA LIMIT |
|-------------------------|--------|--------------------------|
| Supply Current - MSI-2 | IDD | ± 1.0μA |
| Output Current (Sink) | IOL5 | ± 20% x Pre-Test Reading |
| Output Current (Source) | IOH5A | ± 20% x Pre-Test Reading |

TABLE 6. APPLICABLE SUBGROUPS

| CONFORI | MANCE GROUP | MIL-STD-883 METHOD | GROUP A SUBGROUPS | READ AND RECORD |
|-------------------------------|----------------|-----------------------|---------------------------------------|------------------------------|
| Initial Test (Pre | Burn-In) | 100% 5004 | 1, 7, 9 | IDD, IOL5, IOH5A |
| Interim Test 1 | (Post Burn-In) | 100% 5004 | 1, 7, 9 | IDD, IOL5, IOH5A |
| Interim Test 2 | (Post Burn-In) | 100% 5004 | 1, 7, 9 | IDD, IOL5, IOH5A |
| PDA (Note 1) | | 100% 5004 | 1, 7, 9, Deltas | |
| Interim Test 3 (Post Burn-In) | | 100% 5004 | 1, 7, 9 | IDD, IOL5, IOH5A |
| PDA (Note 1 |) | 100% 5004 | 1, 7, 9, Deltas | |
| Final Test | | 100% 5004 | 2, 3, 8A, 8B, 10, 11 | |
| Group A | | Sample 5005 | 1, 2, 3, 7, 8A, 8B, 9, 10, 11 | |
| Group B | Subgroup B-5 | Sample 5005 | 1, 2, 3, 7, 8A, 8B, 9, 10, 11, Deltas | Subgroups 1, 2, 3, 9, 10, 11 |
| | Subgroup B-6 | Sample 5005 | 1, 7, 9 | |
| Group D | | Sample 5005 | 1, 2, 3, 8A, 8B, 9 | Subgroups 1, 2 3 |

NOTE: 1. 5% Parameteric, 3% Functional; Cumulative for Static 1 and 2.

TABLE 7. TOTAL DOSE IRRADIATION

| | MIL-STD-883 | IIL-STD-883 | | | READ AND RECORD | | |
|--------------------|-------------|-------------|------------|-----------|-----------------|--|--|
| CONFORMANCE GROUPS | METHOD | PRE-IRRAD | POST-IRRAD | PRE-IRRAD | POST-IRRAD | | |
| Group E Subgroup 2 | 5005 | 1, 7, 9 | Table 4 | 1, 9 | Table 4 | | |



TABLE 8. BURN-IN AND IRRADIATION TEST CONNECTIONS

| | | | | | OSCILLATOR | |
|-------------------------|-------|------------------|-----------------|----------------|------------|---------|
| FUNCTION | OPEN | GROUND | VDD | 9V \pm -0.5V | 50kHz | 25kHz |
| Static Burn-In 1 Note 1 | 3 - 6 | 1, 2, 7 - 15 | 16 | | | |
| Static Burn-In 2 Note 1 | 3 - 6 | 8 | 1, 2, 7, 9 -16 | | | |
| Dynamic Burn-In Note 1 | - | 1, 2, 8 - 10, 15 | 16 | 3 - 6 | 7 | 11 - 14 |
| Irradiation (Note 2) | 3 - 6 | 8 | 1, 2, 7, 9 - 16 | | | |

NOTE:

- 1. Each pin except VDD and GND will have a series resistor of 10K \pm 5%, VDD = 18V \pm 0.5V
- 2. Each pin except VDD and GND will have a series resistor of $47K \pm 5\%$; Group E, Subgroup 2, sample size is 4 dice/wafer, 0 failures, VDD = $10V \pm 0.5V$

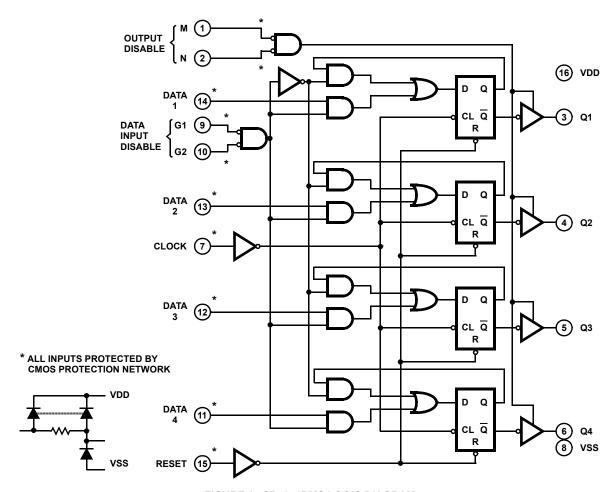


FIGURE 1. CD4076BMS LOGIC DIAGRAM

| | ГΗ | | | |
|--|----|--|--|--|
| | | | | |
| | | | | |

| | | DATA INPUT DISABLE | | DATA | NEXT STATE OUTPUT | |
|-------|-------|--------------------|----|------|----------------------|----|
| RESET | CLOCK | G1 | G2 | D | Q | |
| 1 | X | X | X | X | 0 | |
| 0 | 0 | Х | Х | Х | Q | NC |
| 0 | | 1 | Х | Х | Q | NC |
| 0 | | Х | 1 | Х | Q | NC |
| 0 | | 0 | 0 | 1 | 1 | |
| 0 | | 0 | 0 | 0 | 0 | |
| 0 | 1 | Х | Х | Х | Q | NC |
| 0 | | Х | Х | Х | Q | NC |

When either Output Disable M or N is high, the outputs are disabled (high impedance state), however sequential operation of the flip-flops is not affected.

1 = High Level

X = Don't Care

0 = Low Level

NC = No Change

Typical Performance Characteristics

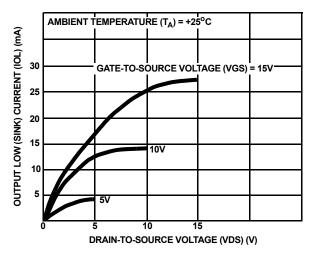
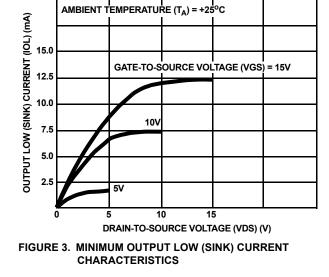


FIGURE 2. TYPICAL OUTPUT LOW (SINK) CURRENT CHARACTERISTICS



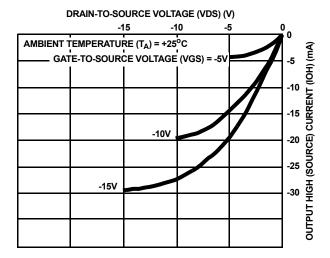


FIGURE 4. TYPICAL OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

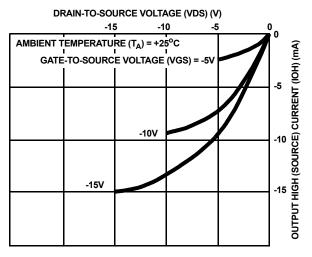


FIGURE 5. MINIMUM OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS



Typical Performance Characteristics (Continued)

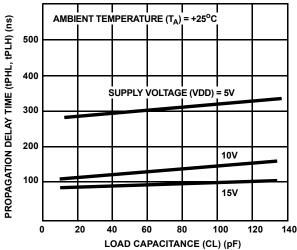


FIGURE 6. TYPICAL PROPAGATION DELAY TIME vs LOAD CAPACITANCE (CLOCK TO Q)

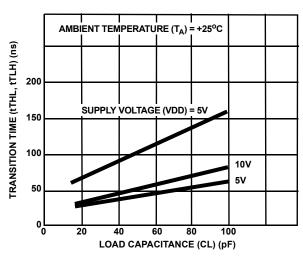


FIGURE 7. TYPICAL TRANSITION TIME vs LOAD CAPACITANCE

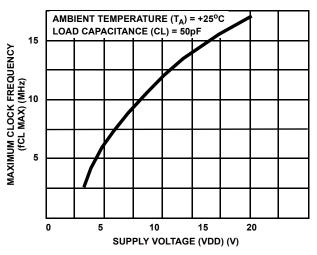


FIGURE 8. TYPICAL MAXIMUM CLOCK INPUT FREQUENCY vs SUPPLY VOLTAGE

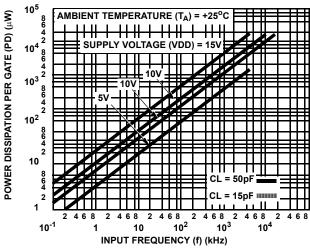
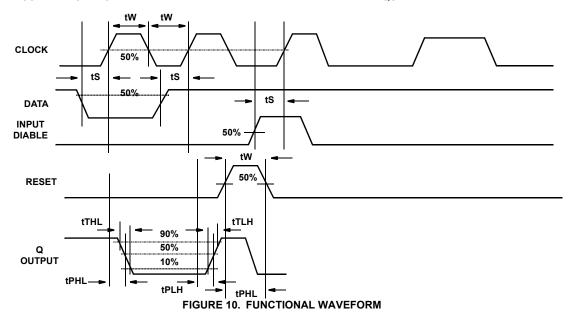
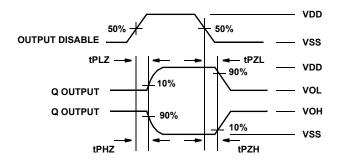


FIGURE 9. TYPICAL DYNAMIC POWER DISSIPATION vs FREQUENCY

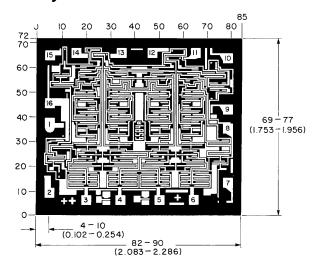




| | TEST | VOLTAGE |
|-----------|------|---------|
| CHARACTER | AT D | AT Q |
| tPHZ | VDD | VSS |
| tPLZ | VSS | VDD |
| tPZL | VSS | VDD |
| tPZH | VDD | VSS |

FIGURE 11. FUNCTIONAL WAVEFORM

Chip Dimensions and Pad Layout



Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10⁻³ inch)

METALLIZATION: Thickness: 11kÅ – 14kÅ, AL.

PASSIVATION: 10.4kÅ - 15.6kÅ, Silane

BOND PADS: 0.004 inches X 0.004 inches MIN **DIE THICKNESS:** 0.0198 inches - 0.0218 inches

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